

2SK1342

Silicon N-Channel MOS FET

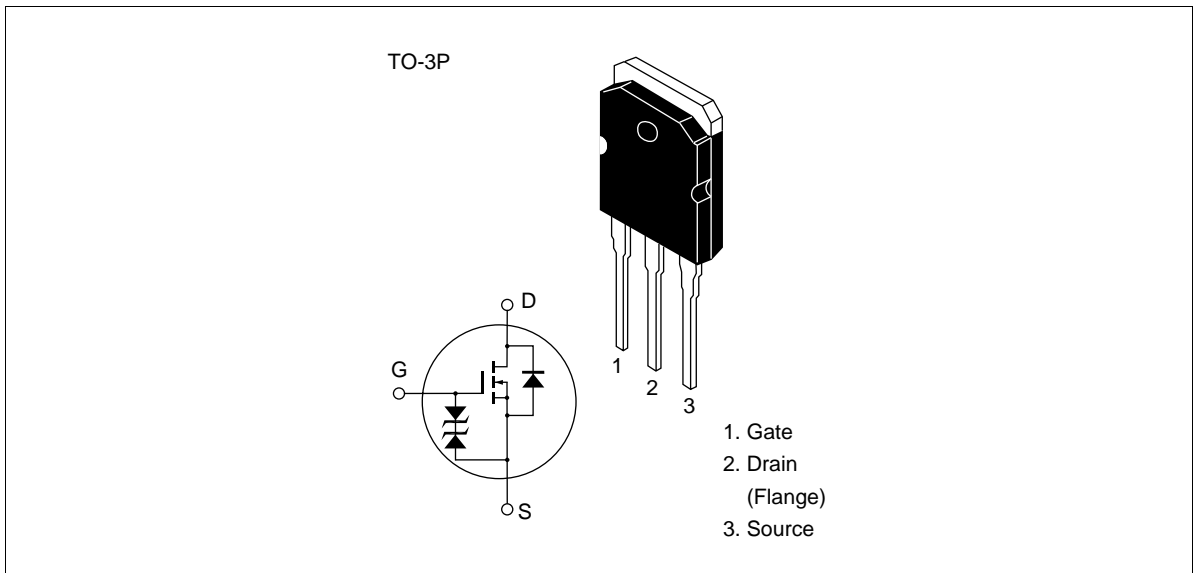
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

Outline



2SK1342

Absolute Maximum Ratings (T_a = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	900	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D	8	A
Drain peak current	I _{D(pulse)} ^{*1}	20	A
Body to drain diode reverse drain current	I _{DR}	8	A
Channel dissipation	P _{ch} ^{*2}	100	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

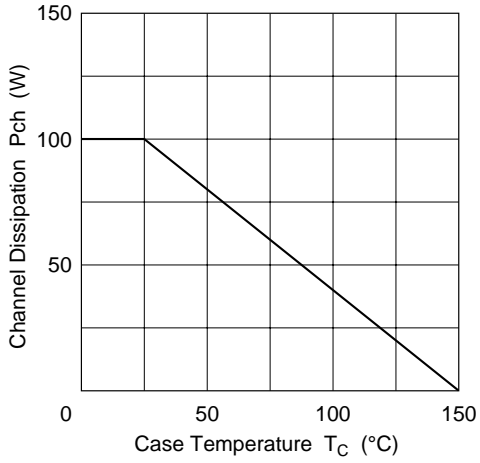
Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%
2. Value at T_c = 25°C

Electrical Characteristics (Ta = 25°C)

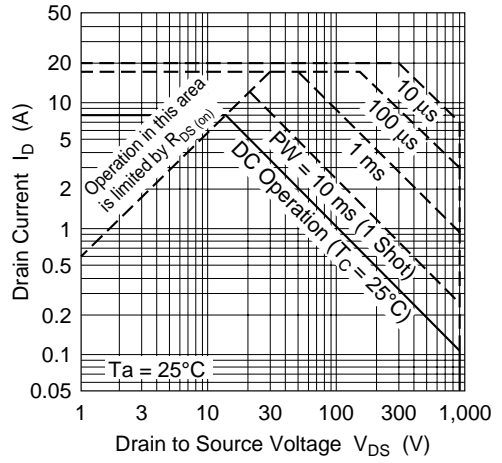
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	900	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 30	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}, V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	250	μA	$V_{DS} = 720 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	—	3.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	1.2	1.6	Ω	$I_D = 4 \text{ A}, V_{GS} = 10 \text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	3.5	5.5	—	S	$I_D = 4 \text{ A}, V_{DS} = 20 \text{ V}^{*1}$
Input capacitance	C_{iss}	—	1730	—	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance	C_{oss}	—	700	—	pF	$f = 1 \text{ MHz}$
Reverse transfer capacitance	C_{rss}	—	310	—	pF	
Turn-on delay time	$t_{d(on)}$	—	25	—	ns	$I_D = 4 \text{ A}, V_{GS} = 10 \text{ V},$
Rise time	t_r	—	135	—	ns	$R_L = 7.5 \text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	—	185	—	ns	
Fall time	t_f	—	130	—	ns	
Body to drain diode forward voltage	V_{DF}	—	0.9	—	V	$I_F = 8 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	900	—	ns	$I_F = 8 \text{ A}, V_{GS} = 0,$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Note: 1. Pulse test

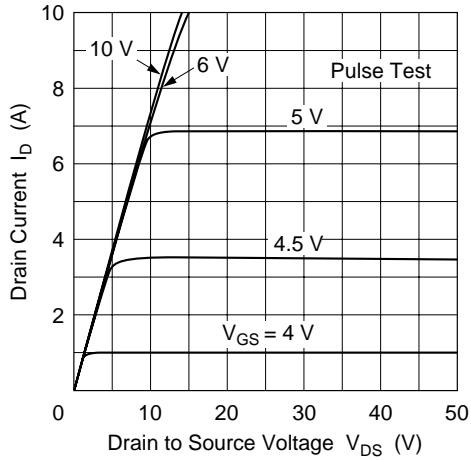
Power vs. Temperature Derating



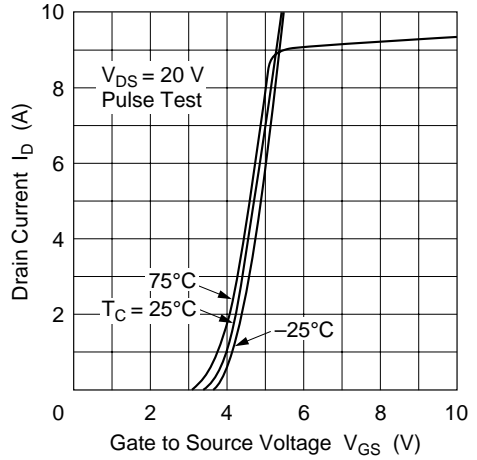
Maximum Safe Operation Area

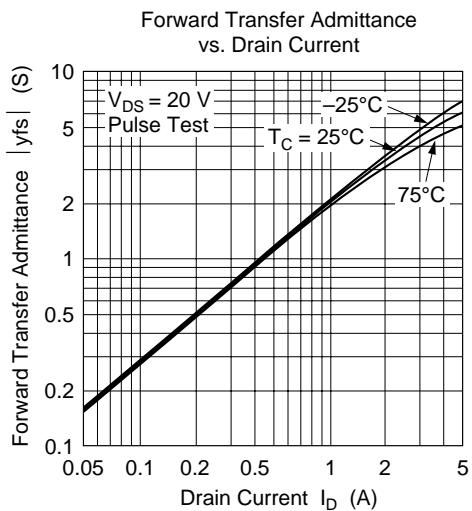
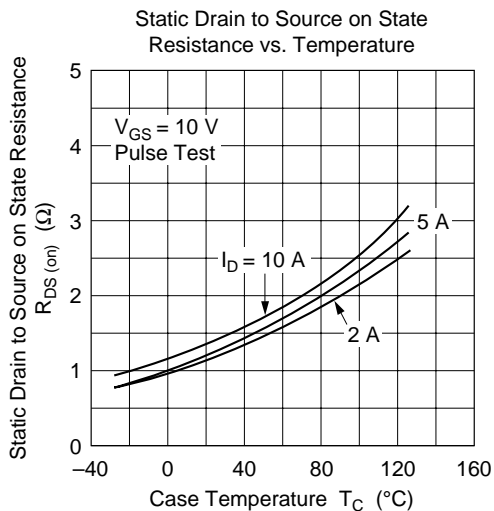
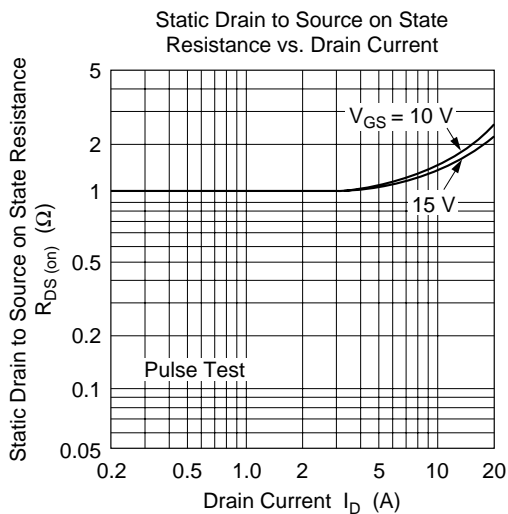
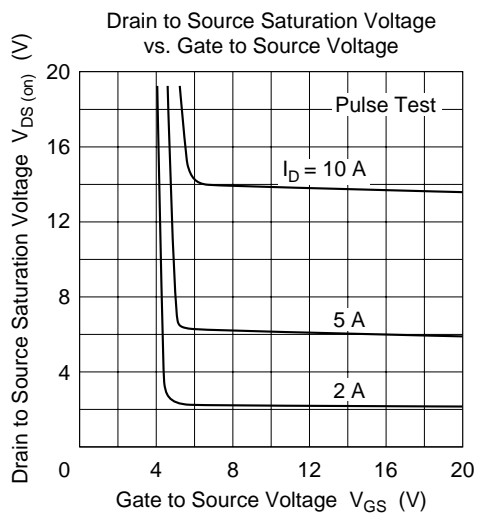


Typical Output Characteristics

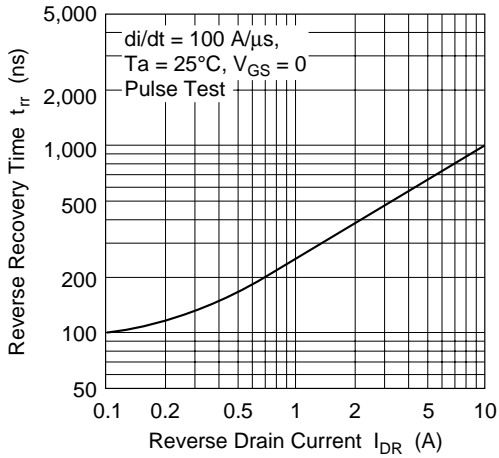


Typical Transfer Characteristics

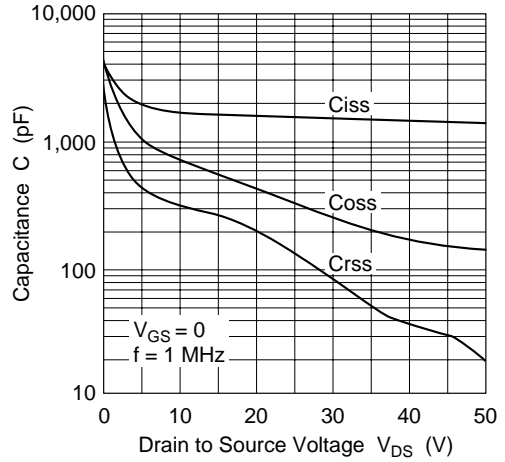




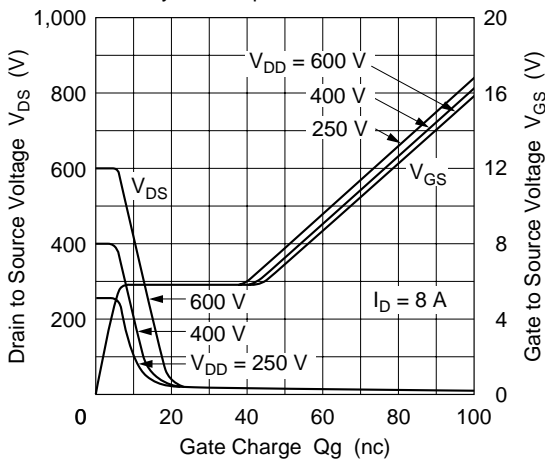
Body to Drain Diode Reverse Recovery Time



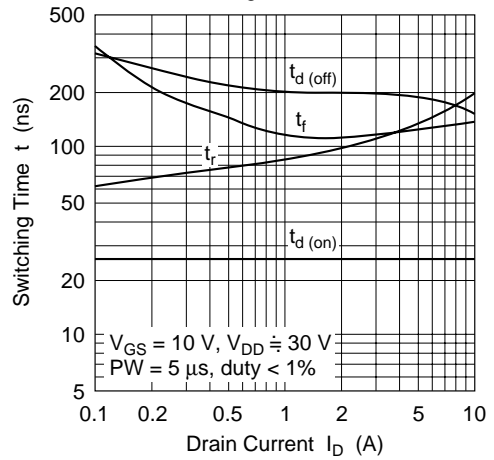
Typical Capacitance vs. Drain to Source Voltage

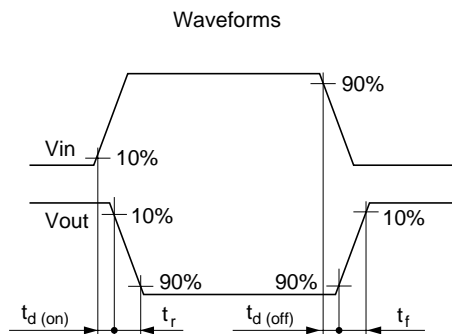
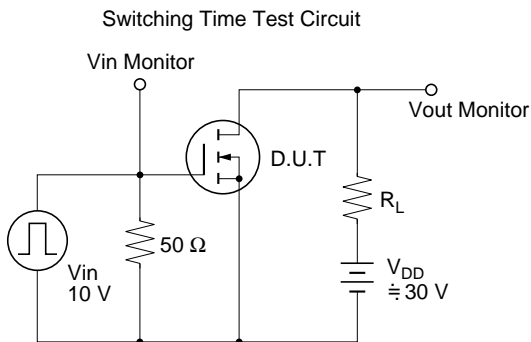
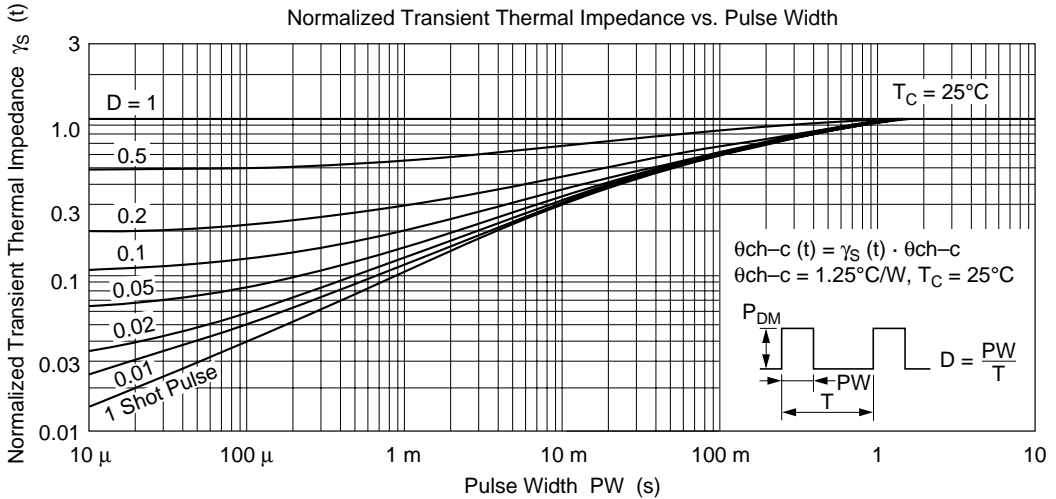
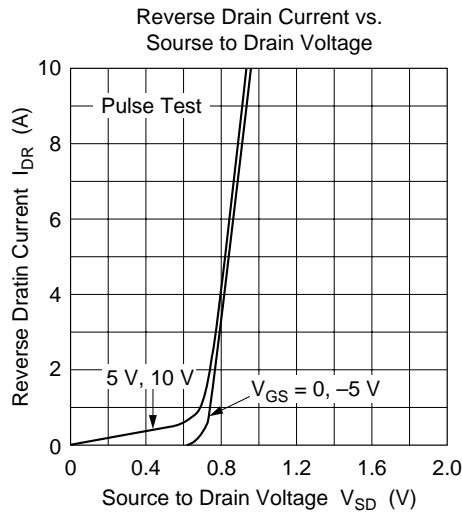


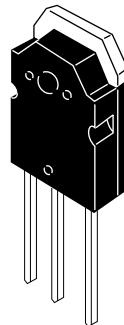
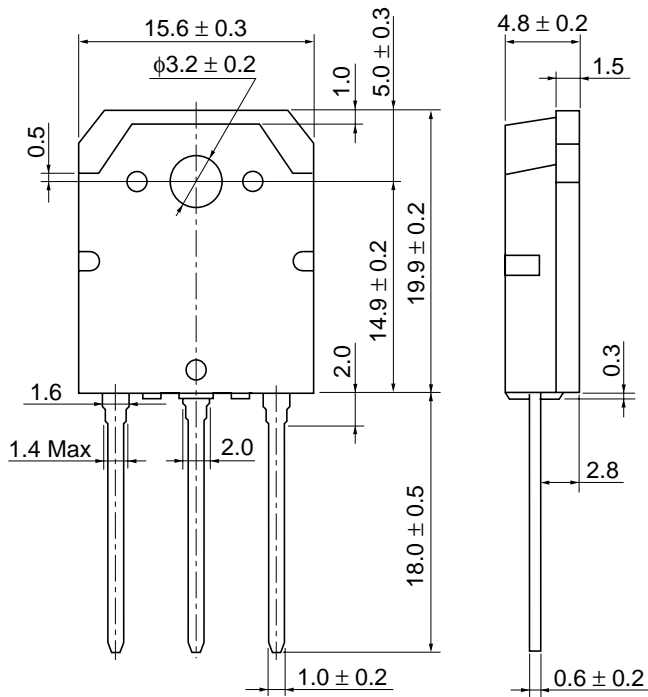
Dynamic Input Characteristics



Switching Characteristics







Hitachi Code	TO-3P
JEDEC	—
EIAJ	Conforms
Weight (reference value)	5.0 g